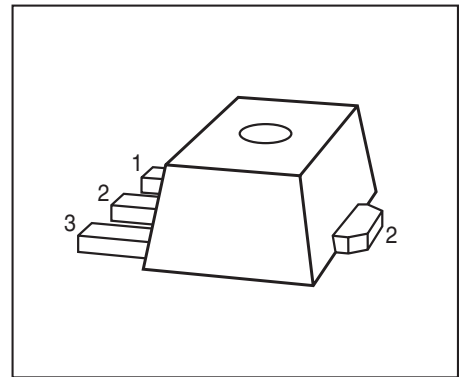


## PNP Silicon AF Transistors

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types: BCX54...BCX56 (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



| Type     | Marking | Pin Configuration |     |     | Package |
|----------|---------|-------------------|-----|-----|---------|
| BCX51    | AA      | 1=B               | 2=C | 3=E | SOT89   |
| BCX51-16 | AD      | 1=B               | 2=C | 3=E | SOT89   |
| BCX52    | AE      | 1=B               | 2=C | 3=E | SOT89   |
| BCX52-16 | AM      | 1=B               | 2=C | 3=E | SOT89   |
| BCX53    | AH      | 1=B               | 2=C | 3=E | SOT89   |
| BCX53-10 | AK      | 1=B               | 2=C | 3=E | SOT89   |
| BCX53-16 | AL      | 1=B               | 2=C | 3=E | SOT89   |

**Maximum Ratings**

| Parameter                                    | Symbol    | Value       | Unit |
|----------------------------------------------|-----------|-------------|------|
| Collector-emitter voltage                    | $V_{CEO}$ |             | V    |
| BCX51                                        |           | 45          |      |
| BCX52                                        |           | 60          |      |
| BCX53                                        |           | 80          |      |
| Collector-base voltage                       | $V_{CBO}$ |             |      |
| BCX51                                        |           | 45          |      |
| BCX52                                        |           | 60          |      |
| BCX53                                        |           | 100         |      |
| Emitter-base voltage                         | $V_{EBO}$ | 5           |      |
| Collector current                            | $I_C$     | 1           | A    |
| Peak collector current, $t_p \leq 10$ ms     | $I_{CM}$  | 1.5         |      |
| Base current                                 | $I_B$     | 100         | mA   |
| Peak base current                            | $I_{BM}$  | 200         |      |
| Total power dissipation<br>$T_S \leq 120$ °C | $P_{tot}$ | 2           | W    |
| Junction temperature                         | $T_j$     | 150         | °C   |
| Storage temperature                          | $T_{stg}$ | -65 ... 150 |      |

**Thermal Resistance**

| Parameter                                | Symbol     | Value     | Unit |
|------------------------------------------|------------|-----------|------|
| Junction - soldering point <sup>1)</sup> | $R_{thJS}$ | $\leq 15$ | K/W  |

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

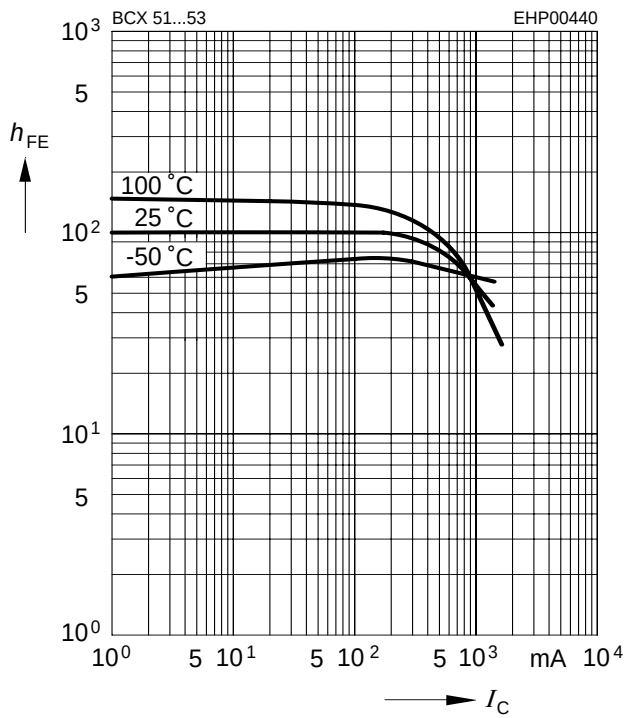
**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

| Parameter                                                                                                                                                                                                                                                                                                                         | Symbol        | Values                      |                           |                             | Unit |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-----------------------------|---------------------------|-----------------------------|------|
|                                                                                                                                                                                                                                                                                                                                   |               | min.                        | typ.                      | max.                        |      |
| DC Characteristics                                                                                                                                                                                                                                                                                                                |               |                             |                           |                             |      |
| Collector-emitter breakdown voltage<br>$I_C = 10\text{ mA}$ , $I_B = 0$ , BCX51<br>$I_C = 10\text{ mA}$ , $I_B = 0$ , BCX52<br>$I_C = 10\text{ mA}$ , $I_B = 0$ , BCX53                                                                                                                                                           | $V_{(BR)CEO}$ | 45<br>60<br>80              | -<br>-<br>-               | -<br>-<br>-                 | V    |
| Collector-base breakdown voltage<br>$I_C = 100\text{ }\mu\text{A}$ , $I_E = 0$ , BCX51<br>$I_C = 100\text{ }\mu\text{A}$ , $I_E = 0$ , BCX52<br>$I_C = 100\text{ }\mu\text{A}$ , $I_E = 0$ , BCX53                                                                                                                                | $V_{(BR)CBO}$ | 45<br>60<br>100             | -<br>-<br>-               | -<br>-<br>-                 |      |
| Emitter-base breakdown voltage<br>$I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$                                                                                                                                                                                                                                                       | $V_{(BR)EBO}$ | 5                           | -                         | -                           |      |
| Collector-base cutoff current<br>$V_{CB} = 30\text{ V}$ , $I_E = 0$<br>$V_{CB} = 30\text{ V}$ , $I_E = 0$ , $T_A = 150\text{ }^\circ\text{C}$                                                                                                                                                                                     | $I_{CBO}$     | -<br>-                      | -<br>-                    | 0.1<br>20                   |      |
| DC current gain <sup>1)</sup><br>$I_C = 5\text{ mA}$ , $V_{CE} = 2\text{ V}$<br>$I_C = 150\text{ mA}$ , $V_{CE} = 2\text{ V}$ , BCX51...BCX53<br>$I_C = 150\text{ mA}$ , $V_{CE} = 2\text{ V}$ , BCX53-10<br>$I_C = 150\text{ mA}$ , $V_{CE} = 2\text{ V}$ , BCX51-16...BCX53-16<br>$I_C = 500\text{ mA}$ , $V_{CE} = 2\text{ V}$ | $h_{FE}$      | 25<br>40<br>63<br>100<br>25 | -<br>-<br>100<br>160<br>- | -<br>250<br>160<br>250<br>- | -    |
| Collector-emitter saturation voltage <sup>1)</sup><br>$I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$                                                                                                                                                                                                                                | $V_{CEsat}$   | -                           | -                         | 0.5                         | V    |
| Base-emitter voltage <sup>1)</sup><br>$I_C = 500\text{ mA}$ , $V_{CE} = 2\text{ V}$                                                                                                                                                                                                                                               | $V_{BE(ON)}$  | -                           | -                         | 1                           |      |
| AC Characteristics                                                                                                                                                                                                                                                                                                                |               |                             |                           |                             |      |
| Transition frequency<br>$I_C = 50\text{ mA}$ , $V_{CE} = 10\text{ V}$ , $f = 20\text{ MHz}$                                                                                                                                                                                                                                       | $f_T$         | -                           | 125                       | -                           | MHz  |

<sup>1)</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

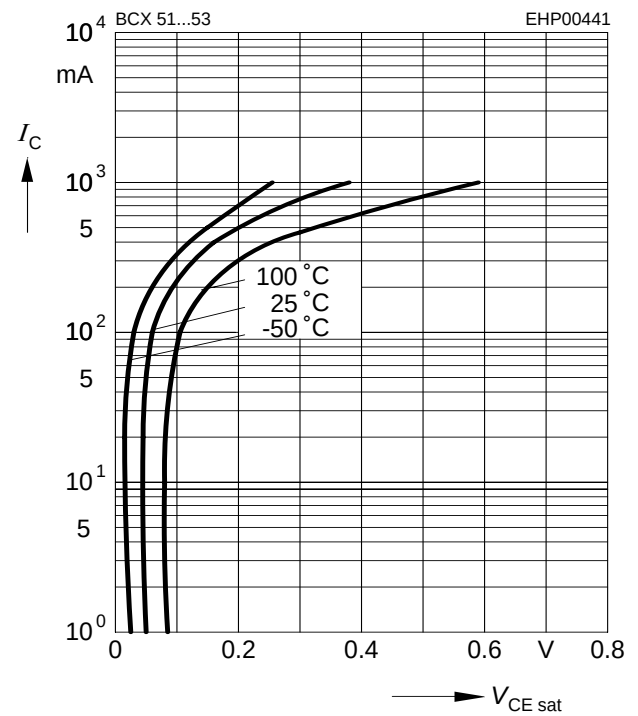
### DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 2 \text{ V}$



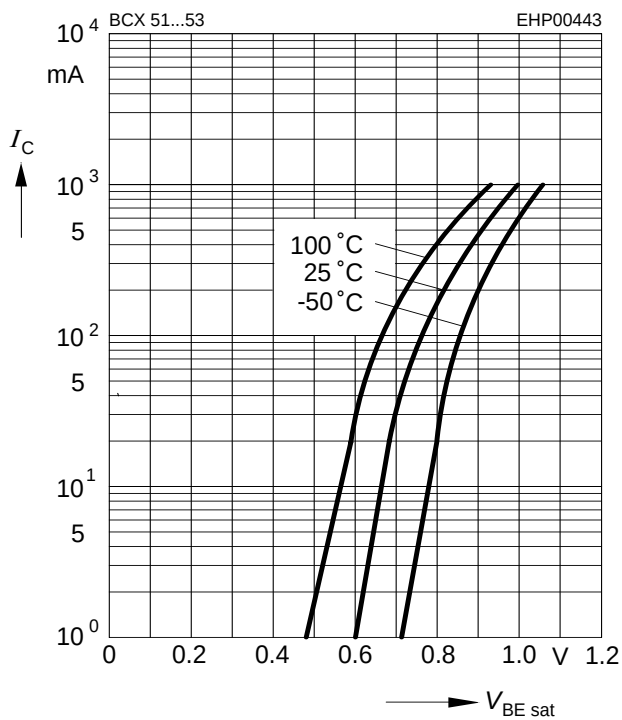
### Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 10$



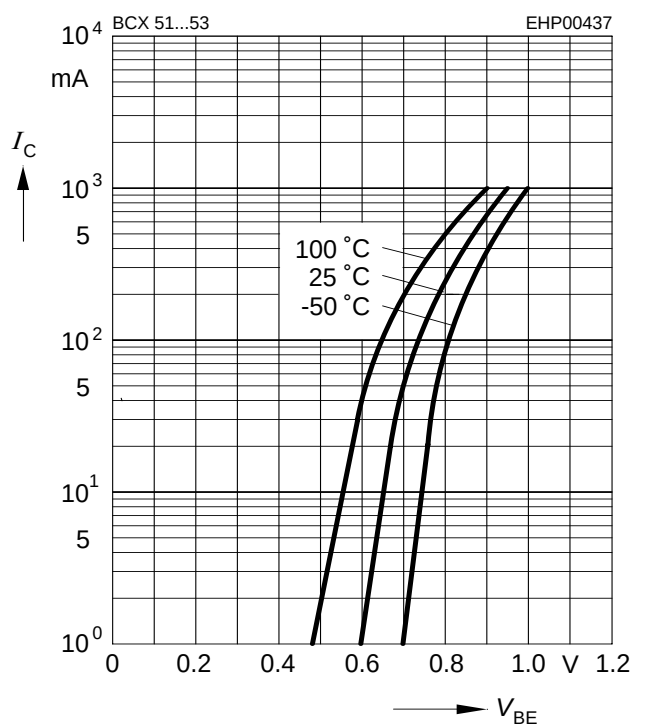
### Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 10$



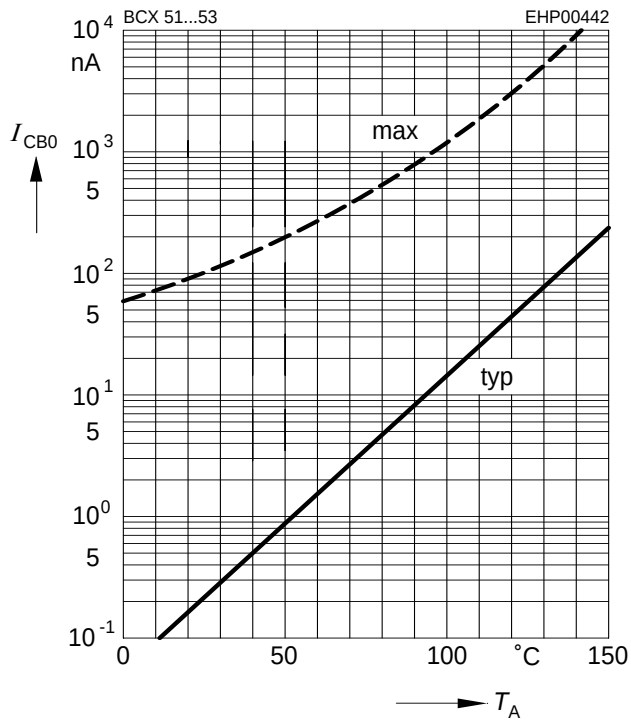
### Collector current $I_C = f(V_{BE})$

$V_{CE} = 2 \text{ V}$



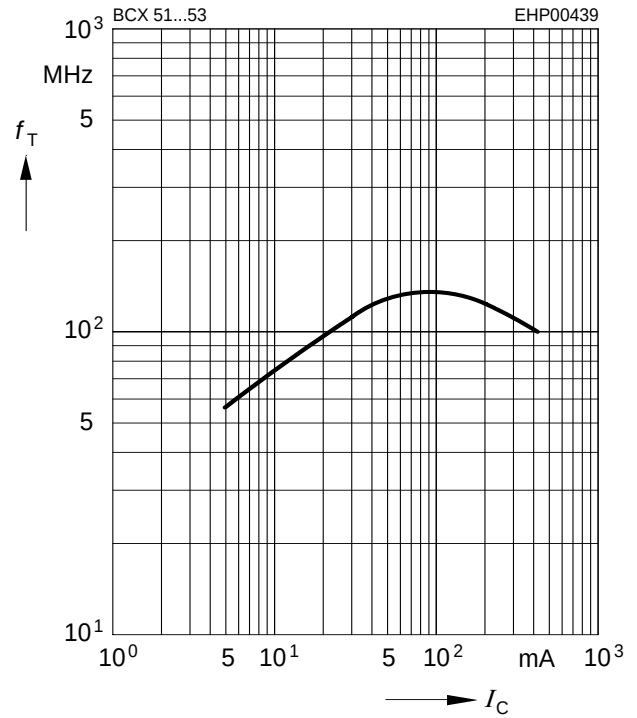
**Collector cutoff current**  $I_{CBO} = f(T_A)$

$V_{CBO} = 30 \text{ V}$

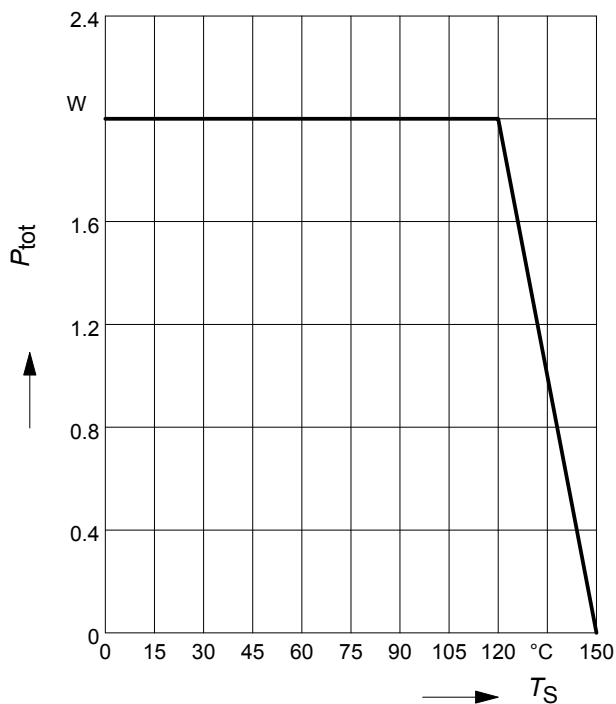


**Transition frequency**  $f_T = f(I_C)$

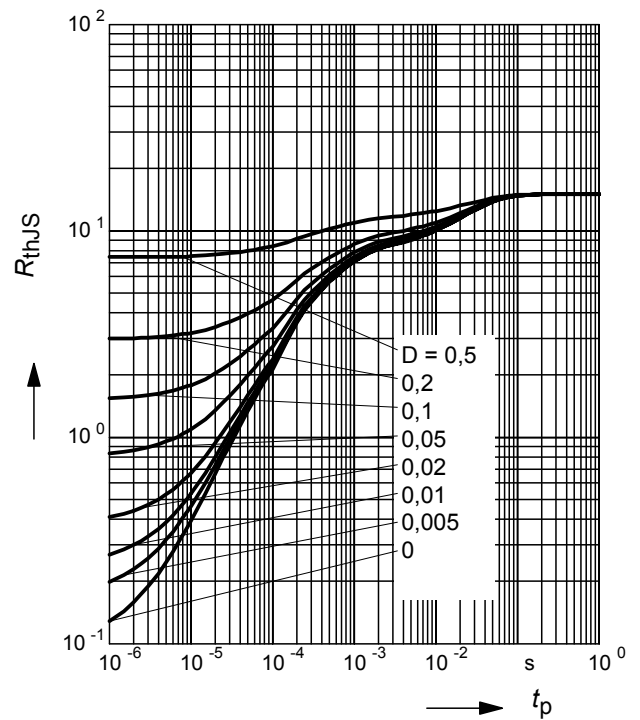
$V_{CE} = 10 \text{ V}$



**Total power dissipation**  $P_{tot} = f(T_S)$

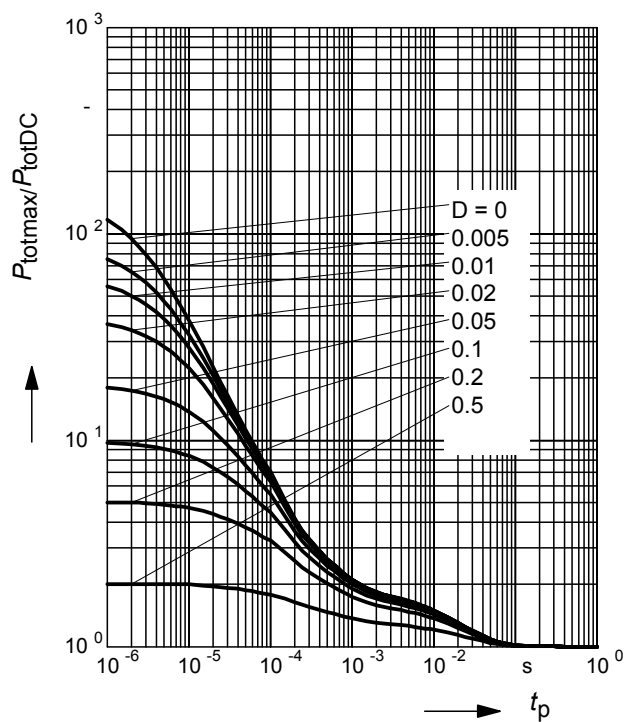


**Permissible Pulse Load**  $R_{thJS} = f(t_p)$

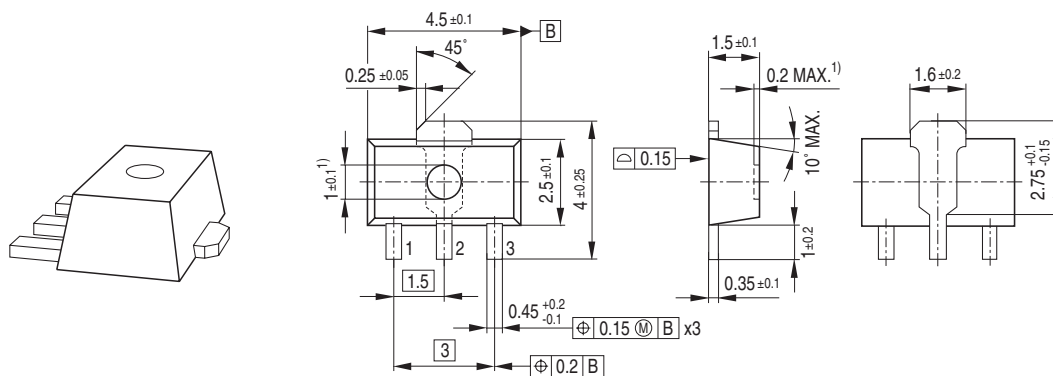


## Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

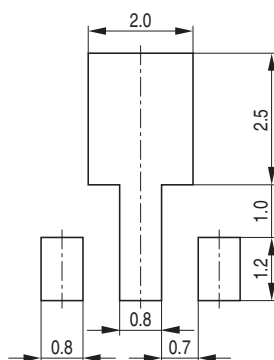


## Package Outline

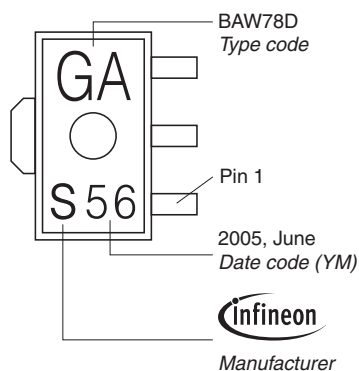


1) Ejector pin markings possible

## Foot Print

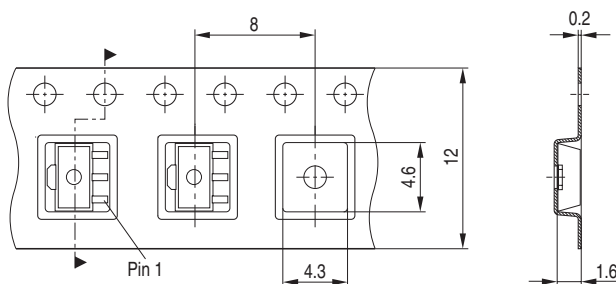


## Marking Layout (Example)



## Standard Packing

Reel ø180 mm = 1.000 Pieces/Reel  
Reel ø330 mm = 4.000 Pieces/Reel



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